CLAIMS:

Applicants propose to cancel claims 17 and 18. No further amendments have been made to the claims. Upon entry by the Examiner, this listing of claims will replace all prior versions and listings of claims in the application.

1. (Previously Presented) An integrated circuit interconnect structure, comprising:

a low K dielectric layer with an upper surface formed over a semiconductor;

a first trench formed in said low K dielectric layer wherein said trench has sidewalls;

a first contiguous barrier layer formed to a thickness X_1 over said upper surface of said low K dielectric layer within said trench and formed to a thickness X_2 on said trench sidewalls wherein X_1 is greater than X_2, wherein the ratio X_1 to X_2 is greater than 3 to 2; and

copper formed over said first contiguous barrier.

2. (Original) The integrated circuit interconnect structure of claim 1 further comprising a second trench comprising sidewalls formed in said low K dielectric layer and separated from said first trench by a distance less than 160 nm.

3. (Original) The integrated circuit interconnect structure of claim 2 wherein said first contiguous barrier layer is formed to a thickness X_2 on said trench sidewalls of said second trench.

4. (Canceled).

5. (Original) The integrated circuit interconnect structure of claim 3 wherein the ratio X_1 to X_2 is greater than 3 to 2.

6. (Previously Presented) The integrated circuit interconnect structure of claim 1 further comprising a second contiguous barrier layer formed over said first contiguous barrier layer and beneath said copper.

7. (Previously Presented) A copper integrated circuit interconnect structure, comprising:

a low K dielectric layer with an upper surface formed over a semiconductor;

a plurality of trenches formed in said low K dielectric layer wherein said plurality of trenches has sidewalls;

a first contiguous barrier layer formed to a thickness X_1 over said upper surface of said low K dielectric layer within said trench and formed to a thickness X_2 over said sidewalls of said plurality of trenches wherein the ratio of X_1 to X_2 is greater than 3 to 2; and

copper formed over said first contiguous barrier.

8. (Original) The integrated circuit interconnect structure of claim 7 wherein said plurality of trenches are separated from each other by a distance of less than 160 nm.

9. (Original) The integrated circuit interconnect structure of claim 7 further comprising a second contiguous barrier layer formed over said first contiguous barrier layer and beneath said copper.

10. (Original) The interconnect structure of claim 7 wherein the dielectric constant of the low K dielectric layer is less than or equal to approximately 3.7.

11. (Previously Presented) A method for forming a copper interconnect structure, comprising:

forming a low K dielectric layer with an upper surface over a semiconductor;

forming a plurality of trenches in said low K dielectric layer wherein said plurality of trenches has sidewalls;

forming a first contiguous barrier layer to a thickness X_1 over said upper surface of said low K dielectric layer within said plurality of trenches and to a thickness X_2 over said sidewalls of said plurality of trenches wherein the ratio of X_1 to X_2 is greater than 3 to 2; and

forming copper over said first contiguous barrier.

12. (Original) The method of claim 11 wherein said plurality of trenches are separated from each other by a distance of less than 160 nm.

13. (Original) The method of claim 12 further comprising forming a second contiguous barrier layer over said first contiguous barrier layer and beneath said copper.

14. (Original) The method of claim 13 wherein the dielectric constant of the low K dielectric layer is less than or equal to approximately 3.7.

15. (Previously Presented) A method for forming an integrated circuit copper interconnect structure, comprising:

forming a low K dielectric layer with a dielectric constant less than or equal to approximately 3.7 with an upper surface over a semiconductor;

forming a plurality of trenches separated by a distance of less than 160 nm in said low K dielectric layer wherein said plurality of trenches has sidewalls;

forming a first contiguous barrier layer to a thickness X_1 over said upper surface of said low K dielectric layer within said plurality of trenches and to a thickness X_2 over said sidewalls of said plurality of trenches wherein the ratio of X_1 to X_2 is greater than 3 to 2; and

forming copper over said first contiguous barrier.

16. (Original) The method of claim 15 further comprising forming a second contiguous barrier layer over said first contiguous barrier layer and beneath said copper.

17. (Canceled).

18. (Canceled).

19. (Withdrawn) The method of claim 11 wherein controlled dielectric pore penetration includes one of a starving of reactants used to deposit the barrier layer and increasing a re-sputter component of barrier layer material, thereby reducing a penetration of reactants into the pores of said trench sidewalls.

20. (Withdrawn) The method of claim 15 wherein controlled dielectric pore penetration includes one of a starving of reactants used to deposit the barrier layer and increasing a re-sputter component of barrier layer material, thereby reducing a penetration of reactants into the pores of said trench sidewalls.